Description

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The 8SLVD1212 is a high-performance differential LVDS fanout buffer. The device is designed for the fanout of high-frequency, very low additive phase-noise clock and data signals.

The 8SLVD1212 is characterized to operate from a 2.5V power supply. Guaranteed output-to-output and part-to-part skew characteristics make the device ideal for clock distribution applications that demand well-defined performance and repeatability.

Two selectable differential inputs and twelve low skew outputs are available. The integrated bias voltage reference enables easy interfacing of single-ended signals to the device inputs.

The 8SLVD1212 is optimized for low power consumption and low additive phase noise.

Features

- Twelve low skew, low additive jitter LVDS output pairs
- Two selectable, differential clock input pairs
- Differential PCLK, nPCLK pairs can accept the following differential input levels: LVDS, LVPECL, CML
- Maximum input clock frequency: 2GHz (maximum)
- LVCMOS/LVTTL interface levels for the control input select pins
- Output skew: 40ps (maximum)
- Propagation delay: 310ps (typical)
- Low additive phase jitter, RMS; f_{REF} = 156.25MHz, 10kHz to 20MHz: 77fs (typical)
- Device current consumption (I_{DD}): 213mA (maximum)
- 2.5V supply voltage
- Lead-free (RoHS 6), 6 × 6 mm, 40-VFQFN packaging
- -40°C to 85°C ambient operating temperature



Block Diagram

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Pin Assignments

Figure 1. Pin Assignments



Pin Descriptions and Characteristics

Table 1. Pin Descriptions^[a]

Number	Name	T	уре	Description	
1	SEL	Input	Pullup/ Pulldown	Reference select control pin. See Table 3 for function. LVCMOS/LVTTL interface levels.	
2	PCLK1	Input	Pulldown	Non-inverting differential clock/data input.	
3	nPCLK1	Input	Pullup/ Pulldown	Inverting differential clock/data input. V _{DD} /2 default when left floating.	
4	V _{REF1}	Output		Bias voltage reference for the PCLK1, nPCLK1 inputs.	
5	V _{DD}	Power		Power supply pins.	
6	V _{DD}	Power		Power supply pins.	
7	V _{REF0}	Output		Bias voltage reference for the PCLK0, nPCLK0 inputs.	
8	nPCLK0	Input	Pullup/ Pulldown	Inverting differential clock/data input. V _{DD} /2 default when left floating.	
9	PCLK0	Input	Pulldown	Non-inverting differential clock/data input.	
10	nc	Unused		Do not connect.	
11	V _{DD}	Power		Power supply pins.	
12	Q0	Output		Differential output pair LVDS interface levels	
13	nQ0	Output		Differential output pair. LVDS interface levels.	
14	Q1	Output		Differential output pair LVDS interface levels	
15	nQ1	Output		Differential output pair. LVDS interface levels.	

Table 1. Pin Descriptions^[a] (Cont.)

Number	Name	Туре	Description	
16	Q2	Output	Differential output pair 11/DS interface loyale	
17	nQ2	Output	Differential output pair. LVDS interface levels.	
18	Q3	Output	Differential output pair. LVDS interface levels.	
19	nQ3	Output		
20	V _{DD}	Power	Power supply pins.	
21	GND	Power	Power supply ground.	
22	Q4	Output	Differential autout pair, LVDS interface lavels	
23	nQ4	Output	Differential output pair. LVDS interface levels.	
24	Q5	Output		
25	nQ5	Output	Differential output pair. LVDS interface levels.	
26	Q6	Output	Differential autout pair LVDC interface lavels	
27	nQ6	Output	Differential output pair. LVDS interface levels.	
28	Q7	Output		
29	nQ7	Output	Differential output pair. LVDS interface levels.	
30	GND	Power	Power supply ground.	
31	V _{DD}	Power	Power supply pins.	
32	Q8	Output	Differential autout pair LVDS interfece levels	
33	nQ8	Output	Differential output pair. LVDS interface levels.	
34	Q9	Output	Differential output pair LVDS interface lovels	
35	nQ9	Output	Differential output pair. LVDS interface levels.	
36	Q10	Output	Differential output pair LVDS interface levels	
37	nQ10	Output	Differential output pair. LVDS interface levels.	
38,	Q11	Output	Differential autout pair LVDS interface laurele	
39	nQ11	Output	Differential output pair. LVDS interface levels.	
40	V _{DD}	Power	Power supply pins.	
	GND_EP	Power	Exposed pad of package. Connect to GND.	

[a] *Pulldown* and *Pullup* refer to internal input resistors. For typical values, see Table 2.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			2		pF
R _{PULLDOWN}	Input Pulldown Resistor			50		kΩ
R _{PULLUP}	Input Pullup Resistor			50		kΩ

Function Table

Table 3. SEL Input Function Table^[a]

SEL	Operation
0	PCLK0, nPCLK0 is the selected differential clock input.
1	PCLK1, nPCLK1 is the selected differential clock input.
Open	Input buffers are disabled and outputs are static.

[a] SEL is an asynchronous control.

Absolute Maximum Ratings

The absolute maximum ratings are stress ratings only. Stresses greater than those listed below can cause permanent damage to the device. Functional operation of the 8SLVD1212 at absolute maximum ratings is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Table 4. Absolute Maximum Ratings

Item	Rating
Supply Voltage, V _{DD}	4.6V
Inputs, V _I	-0.5V to V _{DD} + 0.5V
Outputs, I _O Continuous Current Surge Current	10mA 15mA
Input Sink/Source, I _{REF}	±2mA
Maximum Junction Temperature, T _{J,MAX}	125°C
Storage Temperature, T _{STG}	-65°C to 150°C
ESD - Human Body Model ^[a]	2000V
ESD - Charged Device Mode ^[a]	500V

[a] According to JEDEC/JS-001-2012/ 22-C101E.

DC Electrical Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Power Supply Voltage		2.375	2.5	2.625	V
I _{DD}	Power Supply Current	Q0 to Q11 terminated 100Ω between nQx, Qx		184	213	mA

Table 5. Power Supply DC Characteristics, V_{DD} = 2.5V ±5%, T_A = -40°C to 85°C

Table 6. LVCMOS/LVTTL DC Characteristics, V_{DD} = 2.5V ±5%, T_A = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{MID}	Input voltage		Floating		V _{DD} / 2		V
V _{IH}	Input High Voltage			$0.7 \times V_{DD}$		V _{DD} + 0.3	V
V _{IL}	Input Low Voltage			-0.3		$0.2 \times V_{DD}$	V
I _{IH}	Input High Current	SEL	V _{DD} = V _{IN} = 2.625V			150	μA
IL	Input Low Current	SEL	V _{DD} = 2.625V, V _{IN} = 0V	-150			μA

Table 7. Differential Inputs Characteristics, V_{DD} = 2.5V ±5%, T_A = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
IIH	Input High Current	PCLK0, nPCLK0 PCLK1, nPCLK1	V _{IN} = V _{DD} = 2.625V			150	μA
1	Input	PCLK0, PCLK1	V _{IN} = 0V, V _{DD} = 2.625V	-10			μA
ι _{IL}	Low Current r	nPCLK0, nPCLK1	V _{IN} = 0V, V _{DD} = 2.625V	-150			μA
V _{REF0} , V _{REF1}	Reference Voltage for Input Bias		I _{REFx} = ±0.5mA	(V _{DD} /2) - 0.15	V _{DD} /2	(V _{DD} /2) + 0.15	V
V	V _{PP} Peak-to-Peak Voltage ^[a]		f _{REF} < 1.5GHz	0.1		1.5	V
vРР			f _{REF} > 1.5GHz	0.2		1.5	V
V _{CMR}	Common Mode Input Voltage ^{[a][b]}			1.0		V _{DD} - (V _{pp} /2)	V

[a] V_{IL} should not be less than -0.3V. V_{IH} should not be greater than $V_{DD}.$

[b] Common mode input voltage is defined at the crosspoint.

Table 8. LVDS DC Characteristics, $V_{DD} = 2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{OD}	Differential Output Voltage	Outputs Loaded with 100 Ω	247		454	mV
ΔV_{OD}	V _{OD} Magnitude Change				50	mV
V _{OS}	Offset Voltage		1.125		1.375	V
ΔV_{OS}	V _{OS} Magnitude Change				50	mV

AC Electrical Characteristics

Table 9. AC Electrical Characteristics, $V_{DD} = 2.5V \pm 5\%$, $T_A = -40$ °C to 85°C^[a]

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f _{REF}	Input PCLK[0:1], Frequency nPCLK[0:1]					2	GHz
$\Delta V/\Delta t$	Input Edge Rate	PCLK[0:1], nPCLK[0:1]		1.5			V/ns
t _{PD}	Propagation Delay ^[b]		PCKx, nPCLKx to any Qx, nQx for $V_{PP} = 0.1V$ or 0.3V	200	310	500	ps
<i>t</i> sk(o)	Output Skew ^{[c][d]}					40	ps
<i>t</i> sk(p)	Pulse Skew ^{[e][f]}		f _{REF} = 100MHz, 500MHz, 1GHz, 1.5GHz			80	ps
<i>t</i> sk(pp)	Part-to-Part Skew ^{[d][g]}					300	ps
t _{JIT}	Buffer Additive Phase Jitter, RMS		f _{REF} = 156.25MHz, V _{PP} = 1.0V, Integration Range: 10kHz – 20MHz		77	90	fs
t _R / t _F	Output Rise/ Fall Time		20% to 80% Outputs Loaded with 100 Ω		100	200	ps
MUXISOLATION	Mux Isolation ^{[h}]	f _{REF} = 100MHz		75		dB

[a] Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

[b] Measured from the differential input crosspoint to the differential output crosspoint.

[c] Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the differential crosspoint.

[d] This parameter is defined in accordance with JEDEC Standard 65.

[e] Output pulse skew tsk(p) is absolute difference of the propagation delay times: |t_{PLH} - t_{PHL}|.

[f] Output duty cycle is frequency dependent: odc= input duty cycle +/- ((tsk(p)/2)*(1/output period))*100.

[g] Defined as skew between outputs on different devices operating at the same supply voltage, same frequency, same temperature and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross point.

[h] Qx, nQx outputs measured differentially (for more information, see Figure 10).

Additive Phase Jitter

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the *dBc Phase Noise*. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a *dBc* value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.

Figure 2. Additive Phase Jitter



▶Phase Noise 10.00dB/ Ref 0.000dBc/Hz

As with most timing specifications, phase noise measurements have issues relating to the limitations of the measurement equipment. The noise floor of the equipment can be higher or lower than the noise floor of the device. Additive phase noise is dependent on both the noise floor of the input source and measurement equipment.

Measured using a Rohde and Schwartz SMA100A as the input source.

Parameter Measurement Information

Figure 3. 2.5V LVDS Output Load Test Circuit



Figure 5. Pulse Skew



Figure 7. Part-to-Part Skew



Figure 4. Differential Input Level







Figure 8. Output Rise/Fall Time



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Figure 9. Propagation Delay





Figure 11. Differential Output Voltage Setup

Figure 12. Offset Voltage Setup

Figure 10. MUX Isolation





Applications Information

Recommendations for Unused Input and Output Pins

Inputs

PCLK/nPCLK Inputs

For applications not requiring the use of a differential input, both the PCLK and nPCLK pins can be left floating. Though not required, but for additional protection, a $1k\Omega$ resistor can be tied from PCLK to ground.

Outputs

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, there should be no trace attached.

Wiring the Differential Input to Accept Single-Ended Levels

Figure 13 shows how a differential input can be wired to accept single ended levels. The reference voltage V1 = $V_{DD}/2$ is generated by the bias resistors R1 and R2. The bypass capacitor (C1) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of R1 and R2 might need to be adjusted to position the V1 in the center of the input voltage swing. For example, if the input clock swing is 2.5V and V_{DD} = 2.5V, R1 and R2 value should be adjusted to set V1 at 1.25V.

The values below are for when both the single ended swing and V_{DD} are at the same voltage. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First, R3 and R4 in parallel should equal the transmission line impedance. For most 50 Ω applications, R3 and R4 can be 100 Ω . The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver. When using single-ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however V_{IL} cannot be less than -0.3V and V_{IH} cannot be more than V_{DD} + 0.3V. Suggested edge rate faster than 1V/ns.

Though some of the recommended components might not be used, the pads should be placed in the layout. They can be used for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.

Figure 13. Recommended Schematic for Wiring a Differential Input to Accept Single-ended Levels



2.5V LVPECL Clock Input Interface

The PCLK /nPCLK accepts LVPECL, LVDS, CML and other differential signals. Both signals must meet the V_{PP} and V_{CMR} input requirements. Figure 14 to Figure 18 show interface examples for the PCLK/ nPCLK input driven by the most common driver types. The input interfaces suggested here are examples only. If the driver is from another vendor, use their termination recommendation. Please consult with the vendor of the driver component to confirm the driver termination requirements.

Figure 14. PCLK/nPCLK Input Driven by a CML Driver



Figure 16. PCLK/nPCLK Input Driven by a Built-In Pullup CML Driver

Figure 15. PCLK/nPCLK Input Driven by a 2.5V LVPECL Driver with AC Couple



Figure 17. PCLK/nPCLK Input Driven by a 2.5V LVDS Driver



2.5V Zo = 50Ω PCLK R1 100Ω PCLK LVPECL Input Ξ

Figure 18. PCLK/nPCLK Input Driven by a 2.5V LVPECL Driver



LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance (Z_T) is between 90 Ω and 132 Ω . The actual value should be selected to match the differential impedance (Z_0) of your transmission line. A typical point-to-point LVDS design uses a 100 Ω parallel resistor at the receiver and a 100 Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source.

The standard termination schematic as shown in Figure 19 can be used with either type of output structure. Figure 20, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.





Figure 20. Optional LVDS Termination



VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 4*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as "heat pipes". The number of vias (i.e., "heat pipes") are application specific and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13 mils (0.30 to 0.33 mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only.

For more information, see the Application Note on the Surface Mount Assembly of Amkor's Thermally/ Electrically Enhance Leadframe Base Package, Amkor Technology.





Power Considerations (8SLVD1212A)

This section provides information on power dissipation and junction temperature for the 8SLVD1212. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 8SLVD1212 is the sum of the core power plus the output power dissipation due to the load. The following is the power dissipation for V_{DD} = 2.5V + 5% = 2.625V, which gives worst case results.

The maximum current at 85°C is as follows:

```
I_{DD\_MAX} = 213mA
Power (core)MAX = V_{DD\_MAX} * I_{DD\_MAX} = 2.625V * 213mA = 559.1mW
Total Power MAX = 559.1mW
```

2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: Tj = θ_{JA} * Pd_total + TA

Tj = Junction Temperature

 θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 33°C/W per Table 10.

Therefore, Tj for an ambient temperature of 85°C with all outputs switching is:

85°C + 0.549W * 33°C/W = 103.1°C. This is below the limit of 125°C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 10. Thermal Resistance θ_{JA} for 40-Lead VFQFN, Forced Convection
--

θ _{JA} (°C/W) vs. Air Flow (m/s)			
Meters per Second	0	1	2
Multi-Layer PCB, JEDEC Standard Test Boards	33°C/W	26.3°C/W	24°C/W

Reliability Information

Table 11. $\,\theta_{JA}\,vs.$ Air Flow Table for a 40-Lead VFQFN, Forced Convection

θ _{JA} (°C/W) vs. Air Flow (m/s)			
Meters per Second	0	1	2
Multi-Layer PCB, JEDEC Standard Test Boards	33°C/W	26.3°C/W	24°C/W

Transistor Count

The transistor count for the 8SLVD1212 is: 7829

Package Outline Drawings

The package outline drawings are located at the end of this document. The package information is the most current data available and is subject to change without revision of this document.

Marking Diagram

	1. Line 1 and 2 indicates the part number.
IDT8SLVD12 12NLGI #YYWW\$	 2. Line 3: "YYWW" is the last digit of the year and week that the part was assembled. "#" denotes sequential lot number. "\$" denotes mark code.
♦ LOT	
	1. Line 1 and 2 indicates the part number.
IDT8SLVD12 12ANLGI #YYWW\$	 2. Line 3: "YYWW" is the last digit of the year and week that the part was assembled. "#" denotes sequential lot number. "\$" denotes mark code.
● LOT	

Ordering Information

Orderable Part Number	Die Revision	Status	Package	Shipping Packaging	Temperature
8SLVD1212NLGI			RoHS 6/6, 6 × 6 mm 40-VFQFN	Tray	-40°C to 85°C
8SLVD1212NLGI8	_	NRND ^[a]		Tape and Reel, Pin 1 orientation: EIA-481-C	-40°C to 85°C
8SLVD1212NLGI/W				Tape and Reel, Pin 1 orientation: EIA-481-D	-40°C to 85°C
8SLVD1212ANLGI	A		RoHS 6/6, 6 × 6 mm 40-VFQFN	Tray	-40°C to 85°C
8SLVD1212ANLGI8				Tape and Reel, Pin 1 orientation: EIA-481-C	-40°C to 85°C
8SLVD1212ANLGI/W				Tape and Reel, Pin 1 orientation: EIA-481-D	-40°C to 85°C

[a] Not recommended for new designs (see PCN # N1711-01). Last time buy: March 18, 2018.

[b] Release to production: November 30, 2017.

Table 12. Pin 1 Orientation in Tape and Reel Packaging

Part Number Suffix	Pin 1 Orientation	Illustration
8	Quadrant 1 (EIA-481-C)	Correct Pin 1 ORIENTATION CARRIER TAPE TOPSIDE (Round Sprocket Holes) CONTRACTOR OF FEED
/W	Quadrant 2 (EIA-481-D)	Correct Pin 1 ORIENTATION CARRIER TAPE TOPSIDE (Round Sprocket Holes)

Revision History

Revision Date	Description of Change
February 2, 2021	 Updated the package outline drawings; however, no mechanical changes were made
December 22, 2017	Updated footnote [a] in Ordering Information
December 19, 2017	 Updated Power Considerations (8SLVD1212A) Updated the two footnotes in Ordering Information
November 22, 2017	Initial release.

Package Outline Drawing



PSC-4115-02 NLG40P2 40-VFQFPN 6.0 x 6.0 x 0.90 mm Body, 0.5mm Pitch Rev.04, Apr 17, 2025



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